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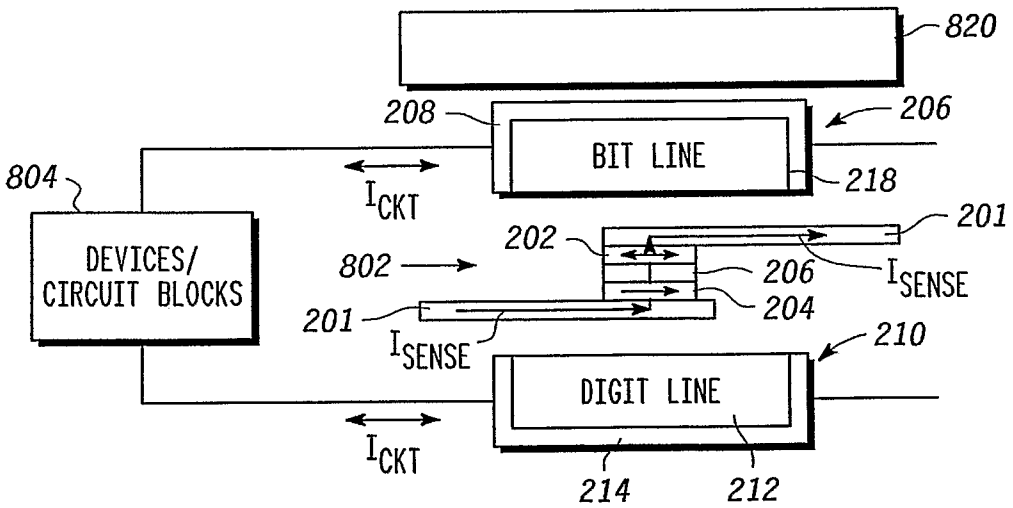
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(54) Title: METHODS OF IMPLEMENTING MAGNETIC TUNNEL JUNCTION CURRENT SENSORS



(57) Abstract: An integrated circuit device (800) is provided which comprises a substrate (801), a conductive line (807) configured to experience a pressure, and a magnetic tunnel junction ("MTJ") core (802) formed between the substrate and the current line. The conductive line (807) is configured to move in response to the pressure, and carries a current which generates a magnetic field. The MTJ core (802) has a resistance value which varies based on the magnetic field. The resistance of the MTJ core (802) therefore varies with respect to changes in the pressure. The MTJ core (802) is configured to produce an electrical output signal which varies as a function of the pressure.

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